Electronic Supplementary Material (ESI) for Nanoscale.

Carrier dynamics at trench defects in InGaN/GaN quantum wells revealed by time-resolved cathodoluminescence

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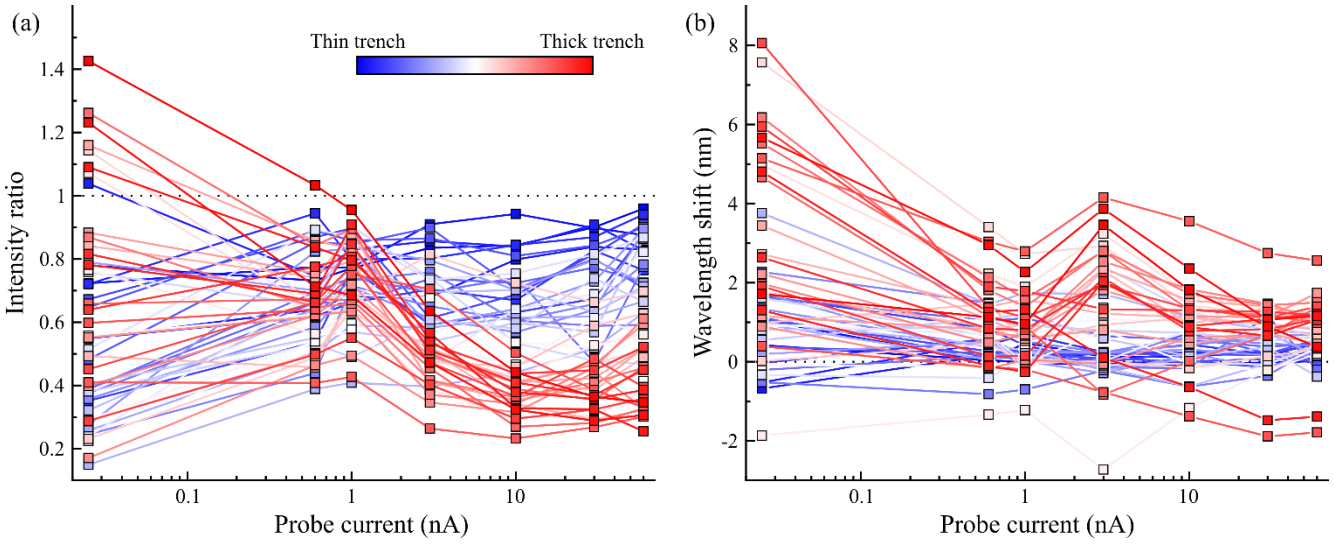

Figure S1. *Plots of the (a) peak intensity ratio and (b) wavelength shift (>0 means redshifted emission) versus probe current for the 50 trench defects analysed, and color-coded with respect to the trench thickness.*

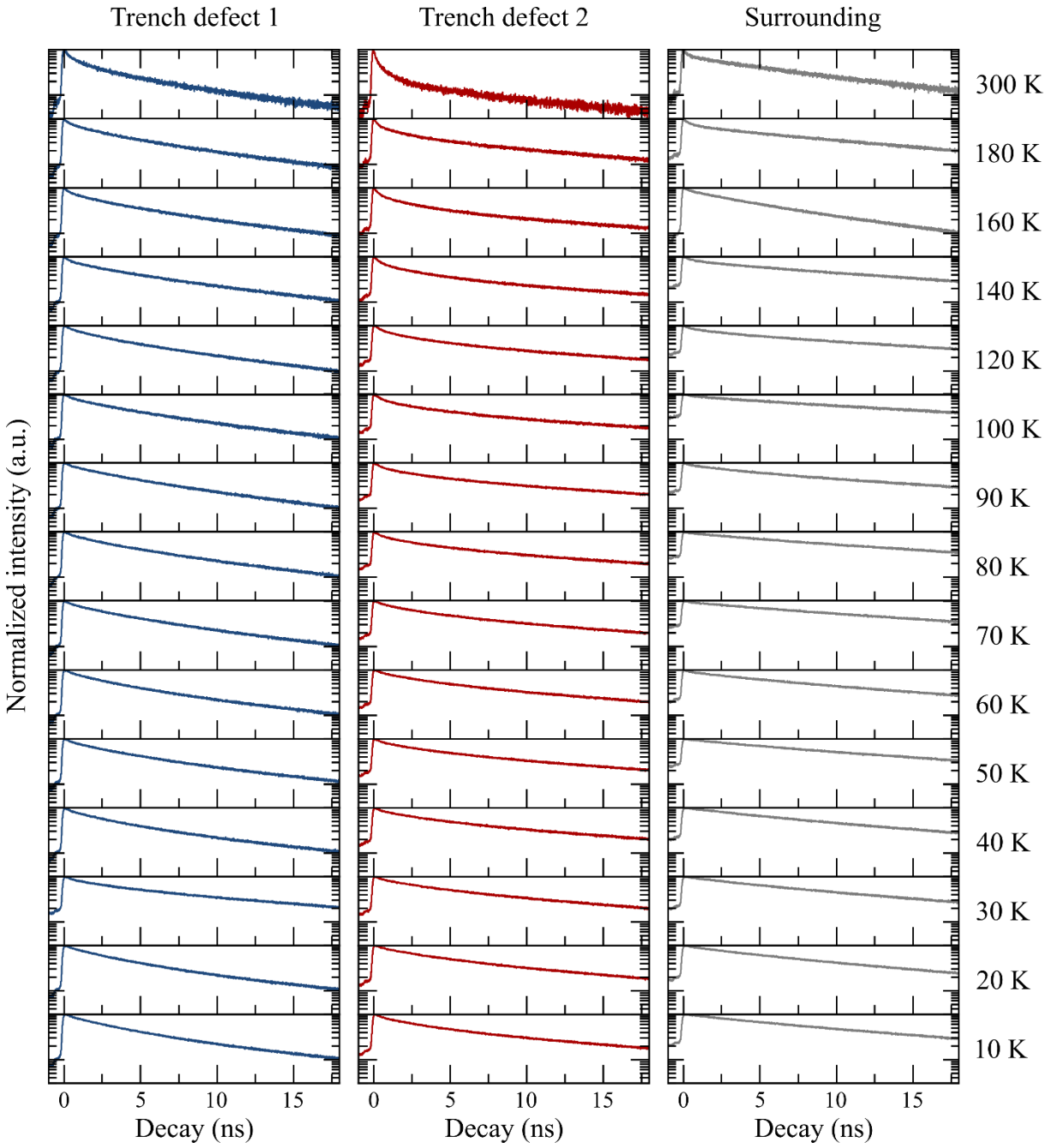

Figure S2. *Time decay curves taken at the peak emission of trench defect 1 (left), trench defect 2 (middle) and surrounding material at temperatures from 10 K to 300 K.*